N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	260mA
$R_{DS(ON)}$(at V_{GS}=10V)	2.5ohm
$R_{DS(ON)}$(at V_{GS}=4.5V)	3.0ohm

Gate-Source ESD Rating Up to 2KV (HBM)

General Description

Trench Power MV MOSFET technology
Voltage controlled small signal switch
Low input Capacitance
Fast Switching Speed
Low Input / Output Leakage
Moisture Sensitivity Level 3
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Battery operated systems
Solid-state relays
Direct logic-level interface TTL/CMOS

Absolute Maximum Ratings (T_A=25 unless otherwise noted)

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250				

Typical Performance Characteristics

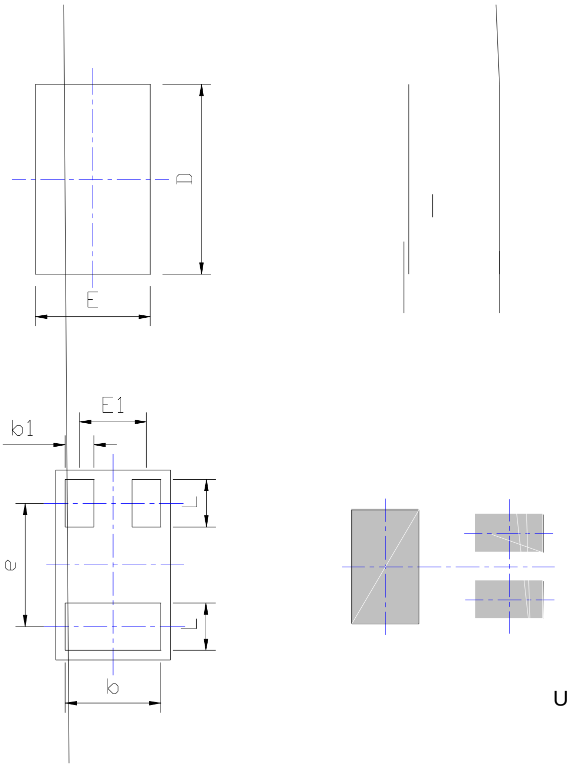
Figure1. Output Characteristics

Figure2. Transfer Characteristics

Figure7. On-Resistance vs V_{GS}

Figure8. Threshold Voltage vs Temperature

DFN1006-3L Package information



UNIT mm